NEW PRODUCT

Lead-free Green

DMN3070SSN

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)\ MAX}$	Package	I_D T_A = +25°C
30V	40mΩ @ V_{GS} = 10V	SC59	5.1A
	50mΩ @ V_{GS} = 4.5V		4.3A

Description

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- DC-DC Converters
- Power Management Functions

Features

- Low On-Resistance
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SC59
- Case Material – Molded Plastic. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.014 grams (approximate)
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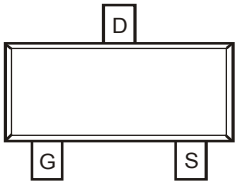
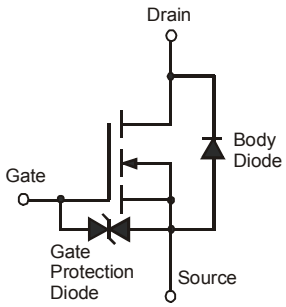


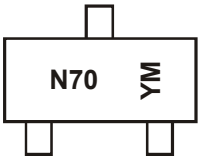


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3070SSN-7	SC59	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html

Marking Information



N70 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: Z = 2012
M = Month ex: 9 = September

Date Code Key

Year	2010	2011	2012	2013	2014	2015	2016	2017
Code	X	Y	Z	A	B	C	D	E

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	4.2 3.3	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	5.1 4	A
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	3.7 2.8	A
	t<10s	T_A = +25°C T_A = +70°C	I_D	4.3 3.3	A
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I_{DM}	60	A
Maximum Body Diode Forward Current (Note 6)			I_S	2	A

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.78	W
	T_A = +70°C		0.5	
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	160	°C/W
	t<10s		115	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	1.3	W
	T_A = +70°C		0.8	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	96	°C/W
	t<10s		68	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	18	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} =24V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±10	µA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1.1	—	2.1	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	24	40	mΩ	V_{GS} = 10V, I_D = 4.2A
		—	30	50		V_{GS} = 4.5V, I_D = 2A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	2.7	—	S	V_{DS} = 5V, I_D =4.2A
Diode Forward Voltage	V_{SD}	—	0.75	1.0	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	697	—	pF	V_{DS} = 15V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	97	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	67	—	pF	
Gate Resistance	R_g	—	1.47	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	6	—	nC	V_{DS} = 15V, I_D = 9A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	13.2	—		
Gate-Source Charge	Q_{gs}	—	2.2	—		
Gate-Drain Charge	Q_{gd}	—	1.8	—		
Turn-On Delay Time	$t_{D(ON)}$	—	4.3	—	ns	V_{DD}=15V,V_{GEN}=10V,R_{GEN} = 6Ω, R_L=15Ω
Turn-Off Delay Time	$t_{D(OFF)}$	—	4.4	—	ns	
Turn-On Rise Time	t_r	—	20.1	—	ns	
Turn-Off Fall Time	t_f	—	4.1	—	ns	
Reverse Recovery Time	t_{rr}	—	7.3	—	Ns	I_F = 9A, di/dt = 500A/µs
Reverse Recovery Charge	Q_{rr}	—	7.9	—	nC	I_F = 9A, di/dt = 500A/µs

Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided. The power dissipation P_D is based on t<10s $R_{\theta JA}$.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided. The power dissipation P_D is based on t<10s $R_{\theta JA}$.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

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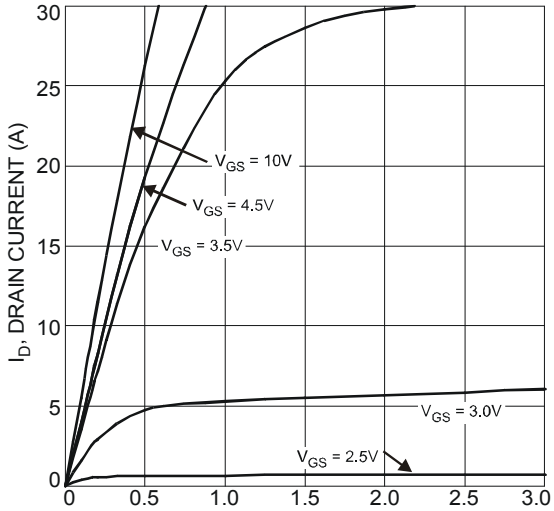

Figure 1 Typical Output Characteristic

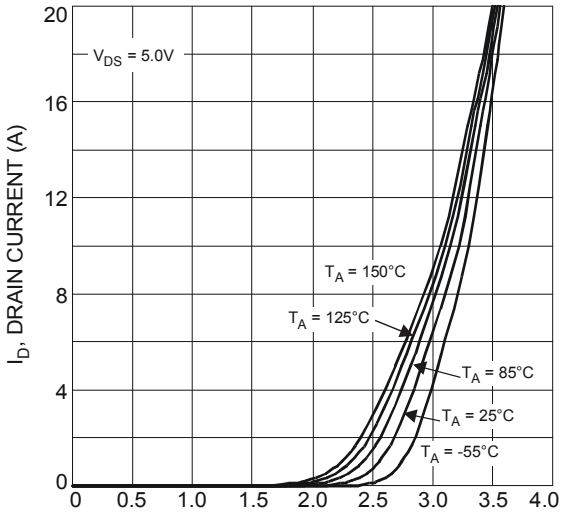

Figure 2 Typical Transfer Characteristics

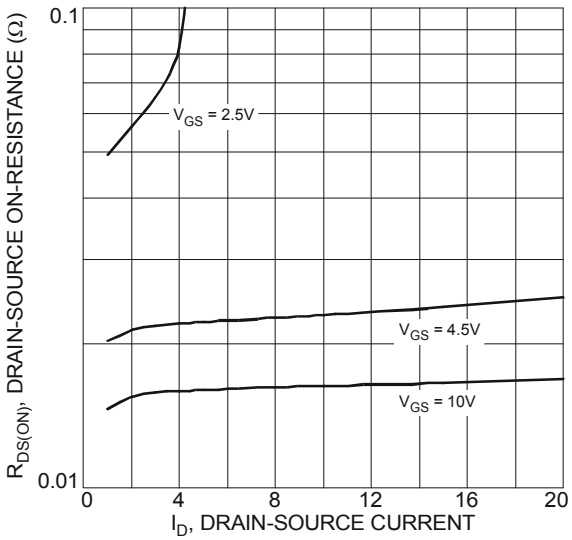

Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

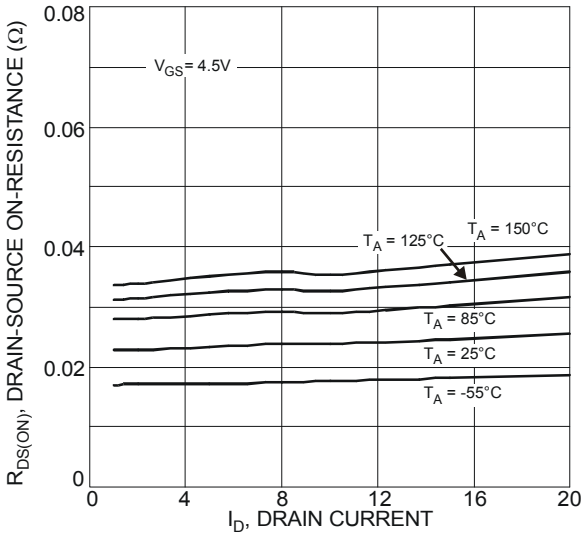

Figure 4 Typical On-Resistance vs. Drain Current and Temperature

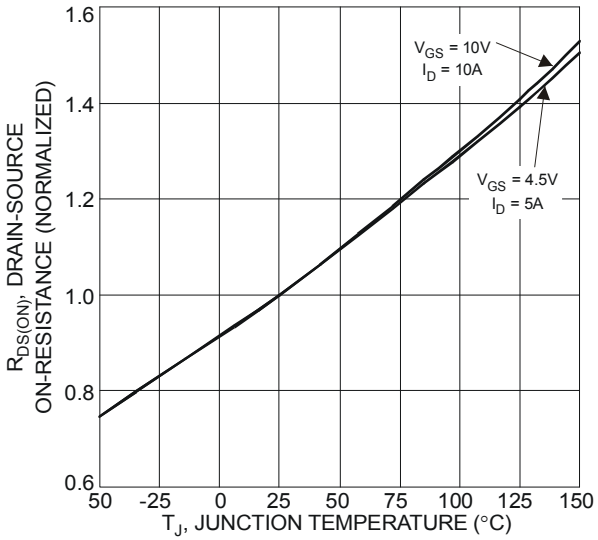

Figure 5 On-Resistance Variation with Temperature

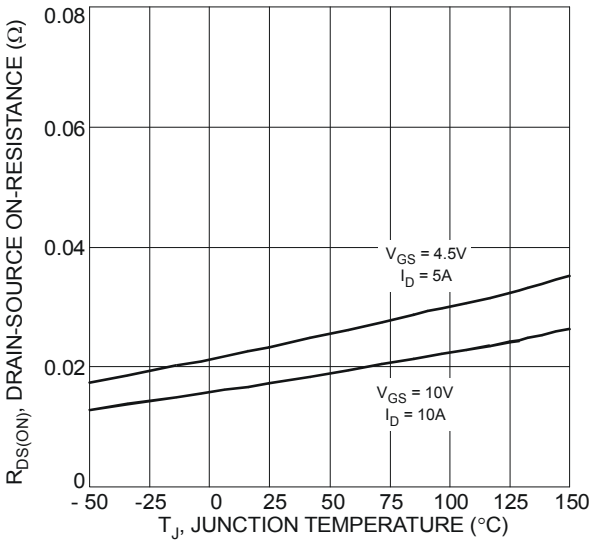

Figure 6 On-Resistance Variation with Temperature

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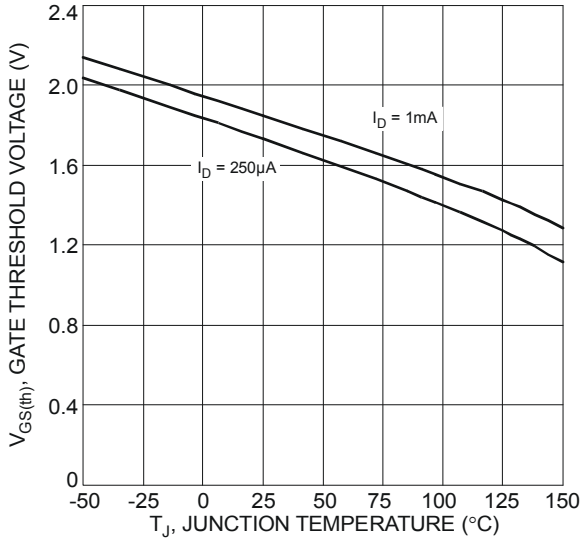

Figure 7 Gate Threshold Variation vs. Ambient Temperature

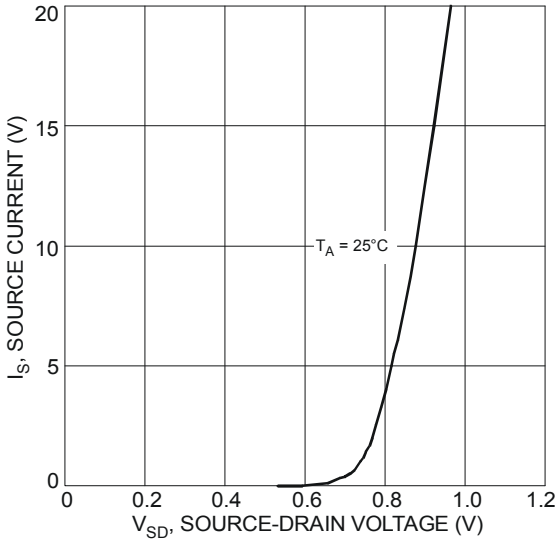

Figure 8 Diode Forward Voltage vs. Current

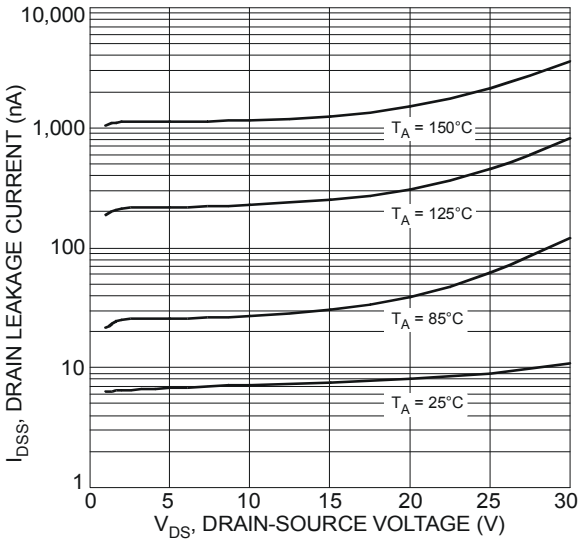

Figure 9 Typical Drain-Source Leakage Current vs. Voltage

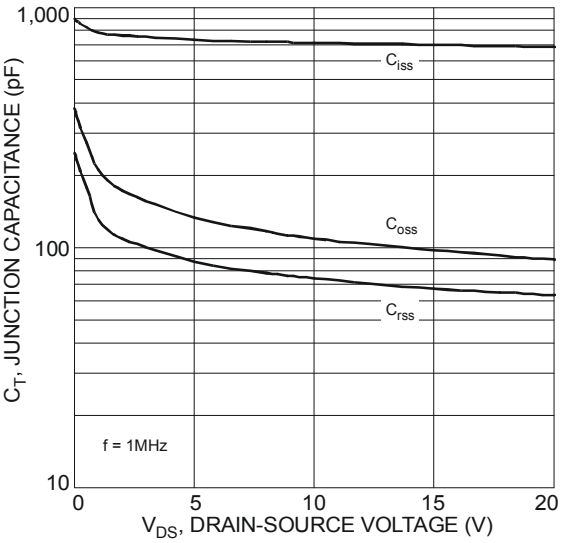

Figure 10 Typical Junction Capacitance

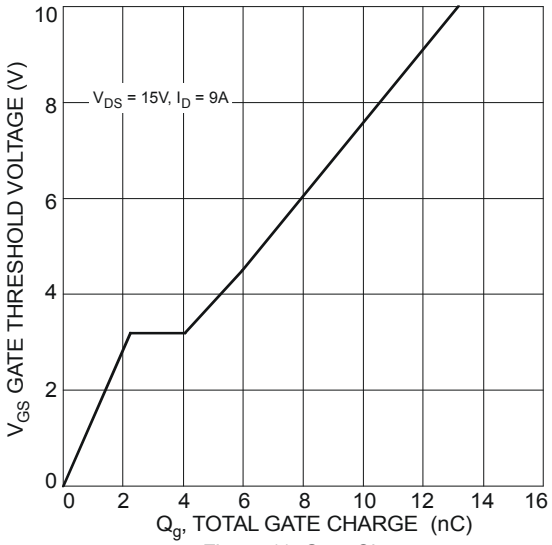

Figure 11 Gate Charge

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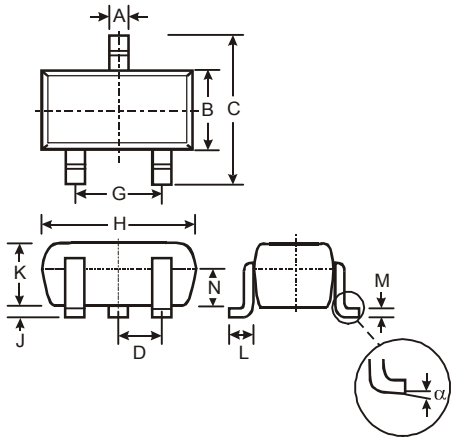
Package Outline Dimensions

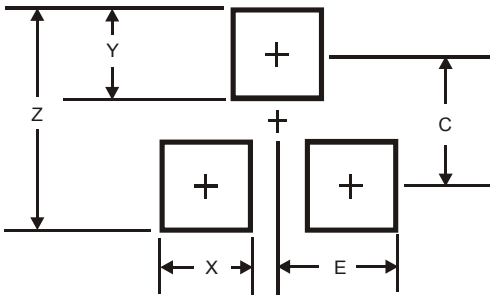
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SC59			
Dim	**Min**	**Max**	**Typ**
A	0.35	0.50	0.38
B	1.50	1.70	1.60
C	2.70	3.00	2.80
D	-	-	0.95
G	-	-	1.90
H	2.90	3.10	3.00
J	0.013	0.10	0.05
K	1.00	1.30	1.10
L	0.35	0.55	0.40
M	0.10	0.20	0.15
N	0.70	0.80	0.75
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.4
X	0.8
Y	1.0
C	2.4
E	1.35

NEW PRODUCT

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